

Spin injection and detection by resonant tunneling structure

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A theory of spin-dependent electron transmission through resonant tunneling diode (RTD) grown of non-centrosymmetrical semiconductor compounds has been presented. It has been shown that RTD can be employed for injection and detection of spin-polarized carriers: (i) electric current flow in the interface plane leads to spin polarization of the transmitted carriers, (ii) transmission of the spin-polarized carriers through the RTD is accompanied by generation of an in-plane electric current. The microscopic origin of the effects is the spin-orbit coupling-induced splitting of the resonant level.

I. INTRODUCTION

Spin-dependent phenomena and particularly transport of spin-polarized carriers in semiconductor heterostructures attract a great attention. One of the key problems of spintronics is a development of efficient methods of injection and detection of spin-polarized carriers. Among various techniques ranging from optical orientation to spin injection from magnetic materials, development of non-magnetic semiconductor injectors and detectors is of the special interest. Spin-orbit interaction underlying such devices couples spin states and space motion of conduction electrons and makes conversion of electric current into spin orientation and vice versa possible.

Recently it was demonstrated that transparency of semiconductor barriers may depend on the spin orientation of carriers. Two microscopic mechanisms, Rashba spin-orbit coupling induced by the barrier asymmetry [1-3] and the k^3 Dresselhaus spin splitting in non-centrosymmetrical materials [4-6], were shown to be responsible for the effect of spin-dependent tunneling. Devices based on spin-dependent tunneling were suggested to be utilized as components of the spin field effect transistor [7].

In this report we present a theory of resonant spin-dependent tunneling through the RTD structure grown of non-centrosymmetrical semiconductors. We show that the RTD can be employed for injection and detection of spin-polarized carriers. The effects originate from the spin-orbit coupling-induced splitting of the resonant level.

II. RESONANT SPIN-DEPENDENT TUNNELING

We consider the transmission of electrons with the initial wavevector $\mathbf{k} = (\mathbf{k}_{\parallel}, k_z)$ through a symmetrical double barrier structure grown along $z \parallel [001]$ direction (see Fig.1). Here $\mathbf{k}_{\parallel}$ is the wavevector in the plane of the interfaces, and k_z is wavevector component normal to the barrier and pointing in the direction of tunnelling. The effective electron Hamiltonian of non-centrosymmetrical semiconductors contains spin-dependent k^3 Dresselhaus term that, for the case of the RTD structure, can be sim-

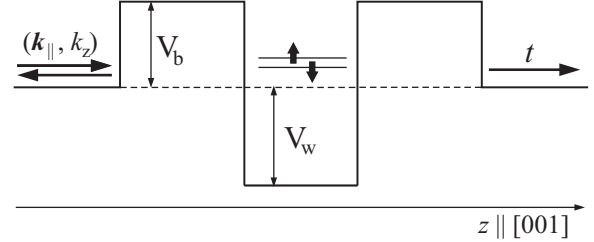


FIG. 1: Electron transmission through RTD structure.

plified to

$$\mathcal{H}_D = \gamma(\hat{\sigma}_x k_x - \hat{\sigma}_y k_y) \frac{\partial^2}{\partial z^2}, \quad (1)$$

where γ is a constant depending on the compound, $\hat{\sigma}_\alpha$ are the Pauli matrices, and the coordinate axes x, y, z are assumed to be parallel to the cubic crystallographic axes [100], [010], [001], respectively. The electron spins $\mathbf{s}_{\pm}$ corresponding to the spin eigen-states " $\pm$ " of the Dresselhaus term (1) depend on the electron wavevector and are given by

$$\mathbf{s}_{\pm} = 1/2 (\mp \cos \varphi, \pm \sin \varphi, 0), \quad (2)$$

where φ is the polar angle of the wavevector $\mathbf{k}$ in the xy plane, $\mathbf{k}_{\parallel} = (k_{\parallel} \cos \varphi, k_{\parallel} \sin \varphi)$.

Solution of the Schrödinger equation with the term $\mathcal{H}_D$ included allows one to derive the transmission, $t_{\pm}$, and reflection, $r_{\pm}$, coefficients for the electrons of the spin states " $\pm$ ". Fig.2 presents the dependencies of the RTD transparency, $|t_{\pm}|^2$, on the incident electron energy along growth direction, $E_z = \hbar^2 k_z^2 / 2m^*$, at certain in-plane wavevector $k_{\parallel}$. The spin splitting of the resonant peak is clearly seen.

In the case of thick barriers the structure transparency demonstrates a sharp peaks and hence can be approximated by δ -functions

$$|t_{\pm}(E_z, k_{\parallel})|^2 \approx \pi \Gamma_{\pm}(k_{\parallel}) \delta[E_z - E_{\pm}(k_{\parallel})], \quad (3)$$

where transmission efficiency, $\Gamma_{\pm}(k_{\parallel})$, and the resonance energy, $E_{\pm}(k_{\parallel})$, can be expanded as

$$E_{\pm}(k_{\parallel}) \approx E_0 \pm \alpha k_{\parallel}, \quad \Gamma_{\pm}(k_{\parallel}) \approx (1 \pm \beta k_{\parallel}) \Gamma_0. \quad (4)$$

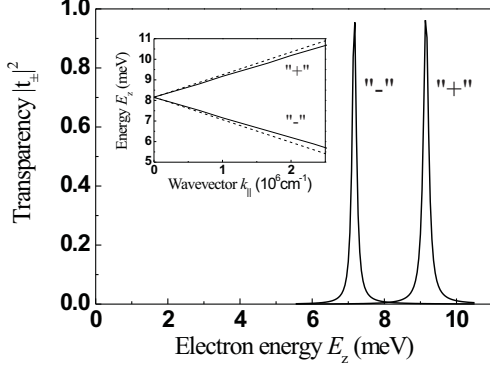


FIG. 2: The RTD transparency, $|t_{\pm}|^2$, as a function of E_z at fixed $k_{\parallel} = 10^6 \text{ cm}^{-1}$. The insert shows the dependence of the spin splitting of the resonant peak on $k_{\parallel}$ calculated numerically (solid curves) and following Eq.(4) (dashed lines). The used parameters, $\gamma = 76 \text{ eV} \cdot \text{\AA}^3$, $m^* = 0.053m_0$, $V_b = 230 \text{ meV}$, $V_w = 200 \text{ meV}$, $a = 29 \text{\AA}$, and $b = 60 \text{\AA}$, correspond to $\text{Al}_x\text{Ga}_{1-x}\text{Sb}$, $x = 0.15/0.3/0/0.3/0.15$, RTD structure.

Here E_0 and Γ_0 are the position and the width of the level when the spin-orbit interaction is neglected, the constants α and β are given by

$$\alpha = \frac{2\gamma m^* V_w + E_0}{\hbar^2} \frac{1}{1 + 2/\kappa a}, \quad \beta = 2 \frac{b m^*}{\hbar^2 \kappa} (\alpha + \gamma \kappa^2),$$

a and b are the well width and the barrier thickness, $\kappa = \sqrt{2m^*(V_b - E_0)}/\hbar$ is the electron wavevector under the barrier, V_w and V_b are the well depth and the barrier height, respectively, and m^* is the effective mass.

III. SPIN INJECTION

Spin splitting of the resonant peak at non-zero $\mathbf{k}_{\parallel}$ can be employed for injection of spin-polarized carriers. We consider two parts of bulk semiconductor separated by a RTD structure. In equilibrium the momentum distribution of incident electrons is isotropic and therefore the average spin of transmitted carriers vanishes. This isotropy can be broken by application, for example, of an in-plane electric field, $\mathbf{F}$. The carriers tunnel now with non-zero average wavevector in the plane of interfaces that leads to the spin polarization of transmitted electrons.

The degree of spin polarization of electrons transmitted through the RTD has the form

$$P_s = \frac{v_d m^*}{\hbar} (\alpha/\varepsilon - \beta), \quad (5)$$

where $v_d = (e\tau_p/m^*)F$ is the drift velocity of the incident particles, e is the electron charge, τ_p is the momentum scattering time, and ε is an energy equal to $E_F - E_0$ for 3D Fermi and $k_B T$ for 3D Boltzmann gas, respectively.

The dependence of the spin polarization, P_s , on the resonant level position, E_0 , is presented in Fig.3 for generate and non-generate 3D electron gas. The change of the sign of P_s with the temperature increasing is related to interplay between the spin splitting, $\alpha k_{\parallel}$, and modification of the widths of the resonant spin sublevels, $\beta k_{\parallel}$.

IV. TUNNELING SPIN-GALVANIC EFFECT

Generation of an electric current by spin-polarized carriers represents the effect inverse to spin injection. Now we assume the electron gas on the left side of the double-barrier structure to be spin-polarized. Electrons with various wavevectors tunnel through the barrier. However due to the splitting of the resonant level, the RTD transparency for the spin-polarized carriers with the certain in-plane wavevector $\mathbf{k}_{\parallel}$ is larger than the transparency for the particles with the opposite in-plane wavevector, $-\mathbf{k}_{\parallel}$. This asymmetry results in the in-plane flow of the transmitted electrons near the barrier, i.e. in the interface electric current.

The interface current generated by transmission of spin-polarized electrons through the RTD structure is given by

$$j_{\parallel} = \frac{e\tau_p m^*}{\pi \hbar^4} \frac{\Gamma_0}{\langle 1/E \rangle} f(E_0) (\alpha - \beta \varepsilon) P_s, \quad (6)$$

where $\langle 1/E \rangle$ is the average value of the reciprocal kinetic energy of the carriers, equal to $3/E_F$ for degenerate and $2/k_B T$ for non-degenerate 3D electron gas, and $f(E)$ is the carrier distribution function.

Fig.4 presents the dependence of the interface current, $j_{\parallel}$, on the energy position of the resonant level, E_0 , for degenerate and non-degenerate electron gas. The direction of the current is determined by the spin orientation of the incident electrons with respect to the crystal axes. In particular, the current $\mathbf{j}_{\parallel}$ is parallel (or antiparallel) to the electron spin, $\mathbf{s}$, if $\mathbf{s}$ is directed along axes $[100]$ or

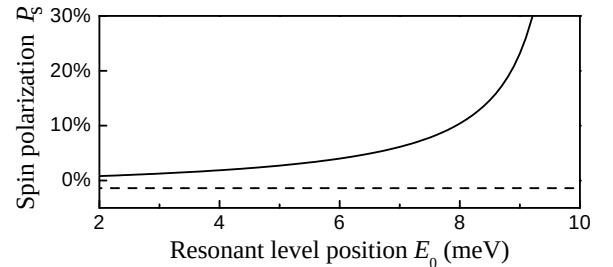


FIG. 3: The spin polarization, P_s , as a function of the resonant level position, E_0 , for Fermi gas with $E_F = 10 \text{ meV}$ (solid curve) and Boltzmann gas at $T = 300 \text{ K}$ (dashed line). The parameters of the double-barrier structure are presented in caption to Fig.2, and $v_d = 5 \cdot 10^6 \text{ cm/s}$.

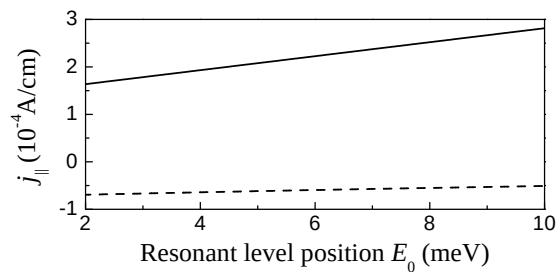


FIG. 4: The interface current, $j_{\parallel}$, as a function of the resonant level position, E_0 , for Fermi gas with $E_F = 10$ meV (solid curve) and Boltzmann gas at $T = 300$ K (dashed line). The parameters are presented in caption to Fig.2, $\tau_p = 1$ ps, and $P_s = 0.1$.

[010]; and $\mathbf{j}_{\parallel}$ is perpendicular to $\mathbf{s}$, if it is directed along $[1\bar{1}0]$ or $[110]$.

In conclusion, the theory of spin-dependent tunneling has been developed for double-barrier structures based on non-centrosymmetrical semiconductors. It has been shown that RTD could be employed for injection and detection of spin-polarized carriers.

Acknowledgments

This work was supported by the RFBR, the INTAS, programs of the RAS, and Foundation "Dynasty" - ICFPM.

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